L Number	Hits	Search Text	DB	Time stamp
37	8	(("6225162") or ("6388305") or ("6168987")	USPAT	2003/04/18 13:51
		or ("6133602") or ("5591681") or ("5436481") or ("6133093") or		i
40	9	("6096604")).PN. (("6225162") or ("6388305") or ("6168987")	USPAT	2003/04/18 13:51
48	9	or ("6133602") or ("5591681") or ("5436481") or ("6133093") or ("6096604")	USTAT	2003/04/10 13:31
-	3	or ("5572050")).PN. (("6004847") or ("5104819") or ("6274428")).PN.	USPAT	2003/04/18 13:37
_	524	(438/255).CCLS.	USPAT;	2002/11/01 10:08
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
-	479	(438/258).CCLS.	USPAT; US-PGPUB; EPO; JPO;	2002/11/01 10:10
-	271	(438/261).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/11/01 10:10
-	1104	(438/257).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/11/01 10:10
_	450	(438/756).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/11/01 10:11
-	116	(438/757).CCLS.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/11/01 10:11
-	308	(438/724).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/01 10:11
-	3039	438/255,258,201,261,257,756,757,724.ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/01 10:15
-	14	438/255,258,201,261,257,756,757,724.ccls. and (ONS or (oxide adj nitride adj silicon))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/01 10:17
_	1	438/255,258,201,261,257,756,757,724.ccls. and ((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide)))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/01 10:18
-	24	(ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/01 10:21
_	13	((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and semiconductor	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/04 10:07

		7 ,		
_	8	(("6004847") or ("5104819") or ("6274428") or ("6180457") or ("6429470") or ("6318267") or ("5572050") or	USPAT	2003/04/07 12:58
-	20	("4775549")).PN. ((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj	USPAT; US-PGPUB;	2002/11/04 10:09
_	10	<pre>oxide))) and (photoresist or mask) (((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and (photoresist or mask)) and</pre>	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/04 10:10
_	191	semiconductor (438/201).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/04 11:17
_	0	((ONO or (oxide adj nitride adj oxide))	DERWENT; IBM_TDB USPAT; JPO	2003/04/07 12:34
_	0	<pre>same (ONS or (oxide adj nitride adj silicon)) same (photoresist or mask)) and (re-oxidiz\$6 or (second adj oxidiz\$6)) ((ONO or (oxide adj nitride adj oxide))</pre>	USPAT; JPO	2003/04/07 12:38
		<pre>same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6))</pre>	HCDAM- TOC	2002/04/07 12:20
-	0	(ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon)) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6)) and	USPAT; JPO	2003/04/07 12:38
_	66	<pre>semiconductor (ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))</pre>	USPAT; JPO	2003/04/07 12:38
_	80283	(ONO or (oxide adj nitride adj oxide)) or	USPAT; JPO	2003/04/07 12:38
_	23	(ONS or (oxide adj nitride adj silicon)) (ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj	USPAT; JPO	2003/04/07 12:38
-	0	silicon)) ((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and	USPAT; JPO	2003/04/07 12:39
. –	0	<pre>(re-oxidiz\$6 or (second adj oxidiz\$6)) ((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj</pre>	USPAT; JPO	 2003/04/07 12:41
_	11	<pre>silicon))) and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6)) ((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj</pre>	USPAT; JPO	2003/04/07 12:40
_	22	silicon))) and (photoresist or mask) and semiconductor ((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj	USPAT; JPO	2003/04/07 12:40
_	36	<pre>silicon))) and (photoresist or mask) and semiconductor ((ONO or (oxide adj nitride adj oxide)) or (ONS or (oxide adj nitride adj silicon)))</pre>	USPAT; JPO	2003/04/07 12:40
_	0	<pre>and (photoresist or mask) and (re-oxidiz\$6 or (second adj oxidiz\$6)) ((ONO or (oxide adj nitride adj oxide))</pre>	USPAT; JPO	2003/04/07 12:41
		<pre>same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (second adj oxidiz\$6)</pre>		
_	0	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and	USPAT; JPO	2003/04/07 12:41
-	10	(second adj oxidiz\$6) (("5756376") or ("5770467") or ("6318267") or ("6004847") or ("6429470") or ("6180457") or ("5104819") or ("5572050")	USPAT	2003/04/08 09:24
		or ("6472259") or ("4775549")).PN.		

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-	1 ("5650344").PN.	USPAT	2003/04/08 09:37
_	5 (("5650344") or ("4698787") or ("4543597")	USPAT	2003/04/08 09:38
	or ("5049514") or ("5083172")).PN.		1

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